

## 2026 IEEE 30th International Semiconductor Laser Conference (ISLC) List of Posters

<b>MoP1</b>	F. T. Albeladi, University of Jeddah: Chirped Multilayer InAs/GaAs Quantum Dot Lasers for Integrated Frequency Combs
<b>MoP2</b>	S. Arafin, The Ohio State University: 2- $\mu\text{m}$ InP-Based Laser for Photonic-Crystal Surface-Emitting Lasers
<b>MoP3</b>	P. Smowton, Cardiff University: Negative Differential Resistance in Multi-Junction VCSELs for Excitable Optical Spiking Dynamics
<b>MoP4</b>	I. K. A. Bhuiyan, Tampere University: Broadband gain in GaSb-based heterostructures with variable-thickness quantum wells
<b>MoP5</b>	Y. Billiet, Universite Claude Bernard Lyon/Université de Montpellier: Transfer printed interband cascade laser on silicon-germanium
<b>MoP6</b>	J. Boschker, Ferdinand-Braun-Institut (FBH): Limits to ZnSe passivation for high power ridge waveguide lasers
<b>MoP7</b>	C.-H. Cheng, National Institute of Information and Communications Technology Japan: 10-GHz Monolithic Dual-Mode DFB Laser with 300-GHz Frequency Spacing for Future THz Wireless Transmission in B5G/6G Networks
<b>MoP8</b>	M. Dammak, III-V Lab Nokia: Demonstration of hybrid extended cavity laser made of GaAs optical Amplifier and Distributed Bragg Reflector around 965nm
<b>MoP9</b>	K. Ebadi, Aalto University: Regrowth Free Active-Passive Integration on GaAs with Vertical Twin Waveguides
<b>MoP10</b>	A. Elnahal, Ferdinand-Braun-Institut (FBH): Gain-switched picosecond pulse generation from oxide-free electrically pumped VECSELs
<b>MoP11</b>	H. Elsayed, Tampere University: UV-curable adhesive-based edge coupling strategies for Hybrid Integrated Lasers
<b>MoP12</b>	J. Fu, University of Hong Kong: Cladding-free GaN-based Laser Diodes with High Optical Confinement via Flip-Chip Thin-Film Architecture
<b>MoP13</b>	J. Fuchsberger, TU Wien/Harvard University: Continuously Tunable Semiconductor Ring Array Lasers Platform for Broadband Single Mode coverage in the mid IR
<b>MoP14</b>	M. Gioannini, Politecnico di Torino: Understanding Relative Intensity Noise in high-speed multi-mode VCSELs with and without polarization control
<b>MoP15</b>	G. Gomółka, Wroclaw University of Science and Technology: Intrinsic radio frequency noise conversion inside an interband cascade laser frequency comb
<b>MoP16</b>	J. Goutorbe, Université de Montpellier: Performance improvements of interband cascade laser grown on Si with hybrid cladding
<b>MoP17</b>	G. Graziano, Coherent/University of Glasgow: High order mode selection in ring shaped lithographic apertures
<b>MoP18</b>	F. Grillot, Institut Polytechnique de Paris: Impact of excited-state on the self-pulsating dynamics in InAs/GaAs quantum dot laser
<b>MoP19</b>	D. Gvozdic, University of Belgrade: All-optical nonlinear activation unit based on coupled SOA-DFB laser



<b>MoP20</b>	Z. Ikonic, University of Leeds: Optical gain analysis in strained bulk GeSn for mid-infrared photonics
<b>MoP21</b>	T. Ishida, RIKEN: Toward high-power and high-temperature operation of GaAs/AlGaAs THz-QCLs with optimized active regions
<b>MoP22</b>	G. Jandu, Cardiff University: Asymmetric Tapers for Multimode Interference Reflector Lasers
<b>MoP23</b>	H. Jeong, University of Delaware: Low loss quantum dots laser coupling with multi-layer reconfigurable silicon photonic chiplet
<b>MoP24</b>	H. Kahle, The University of New Mexico: Membrane external-cavity surface-emitting lasers (MECSELs): From semiconductor membrane microchip lasers to high-power applications
<b>MoP25</b>	J.-P. Koester, Ferdinand-Braun-Institut (FBH): Monolithic GaAs ring resonator-based Vernier laser
<b>MoP26</b>	M. Kondow, The University of Osaka: Theoretical study on directional output control in Circular Defect in 2D-PhC (CirD) lasers via sub-cavity coupling
<b>MoP27</b>	A. Matsumoto, National Institute of Information and Communications Technology Japan: Experimental Verification of Defect Tolerance in 1.55- $\mu\text{m}$ -Band Quantum Dot Laser Diodes
<b>MoP28</b>	B. Namvar, Tampere University: Thermal behavior of a dual-wavelength intra-cavity contact VCSEL for cryogenic operation
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<b>MoP30</b>	M. Osinski, University of New Mexico: Characterization of 1.55- $\mu\text{m}$ Multiple-Quantum-Well Diode Lasers at Cryogenic Temperatures Down to 10 K
<b>MoP31</b>	C. Papapanos, University of California Berkeley: Single mode operation of Berkeley Surface Emitting Laser (BerkSEL) under arbitrary pump rate
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<b>MoP46</b>	K. Takeda, FUJIFILM Business Innovation Corp: 200Gbps/ch 1060nm Metal-aperture Single-mode VCSEL with Robust 75°C Operation
<b>MoP47</b>	T. Tsukada, Toshiba Corporation Production Innovation Technology Center: Characterization of Photonic Crystal Quantum Cascade Detectors Operating at Room Temperature
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<b>MoP54</b>	R. Wang, Sun Yat-sen University: High-power and large-gain butterfly-packaged C-band SOA based on coupled waveguide
<b>MoP55</b>	H. Wenzel, Ferdinand-Braun Institut (FBH): Numerical investigation of two-photon absorption in high-power lasers
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<b>MoP57</b>	J.-L. Xiao, Chinese Academy of Sciences: Tri-transverse-mode self-chaotic microcavity lasers
<b>MoP58</b>	T. Yanagimoto, University of Miyazaki: Fabrication and Characterization of Sb-based Type-II Quantum Well Lasers Emitting at 1.3 $\mu$ m on GaAs Substrates
<b>MoP59</b>	S. Yanase, Aoyama Gakuin University/National Institute of Information and Communications Technology Japan: 1 THz Mode Spacing of Asymmetric Colliding-pulse Mode-locked Laser Diode with Highly-stacked Quantum Dots

